Silicon NPN Power Transistors 2SD1136

DESCRIPTION

·With TO-220C package

·High collector-base breakdown voltage

: V_{CBO}=200V(min)

APPLICATIONS

·For power switching and TV vertical deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

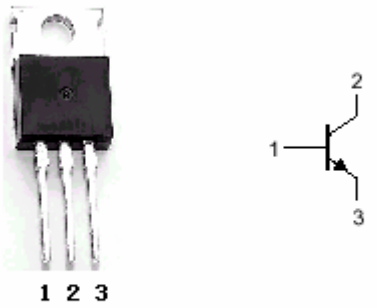

Fig.1 simplified outline (TO-220C) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	200	V
V_{CEO}	Collector-emitter voltage	Open base	80	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		4	A
I_{CM}	Collector current-Peak		5	A
P_C	Collector power dissipation	T_a=25□	1.8	W
		T_C=25□	30	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-45~150	□

CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=50mA; I_B=0	80			V
$V_{(BR)EBO}$	Emitter-base breakdown votage	I_E=1mA; I_C=0	5			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=4 A;I_B=0.4 A			1.5	V
V_{BEsat}	Base-emitter saturation voltage	I_C=4 A;I_B=0.4 A			1.5	V
I_{CEO}	Collector cut-off current	V_{CE}=200V; I_B=0			50	⌠A
I_{EBO}	Collector cut-off current	V_{EB}=5V; I_C=0			50	⌠A
h_{FE}	DC current gain	I_C=4A ; V_{CE}=5V	20			

PACKAGE OUTLINE

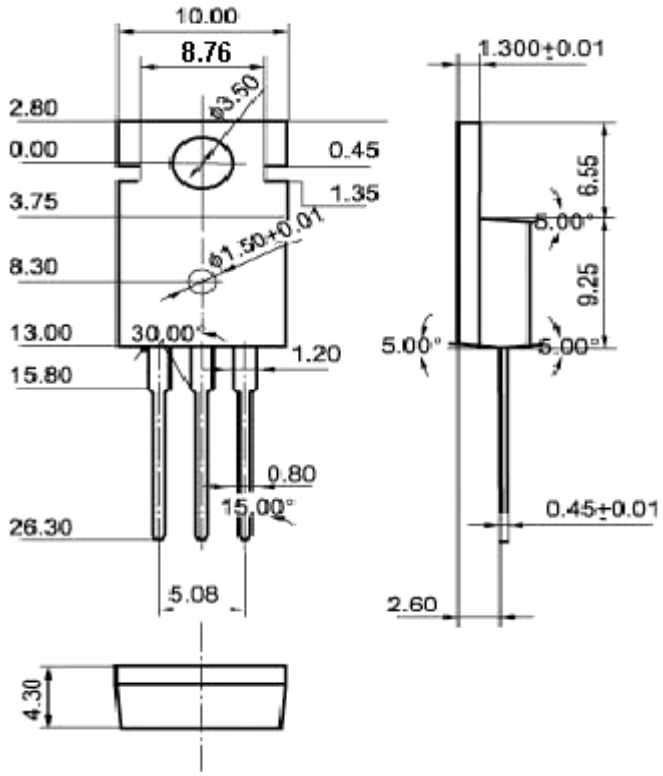

Fig.2 Outline dimensions (unindicated tolerance:±0.10 mm)